

Title (en)
MOSFET IN SILICON CARBIDE

Publication
EP 0386085 A4 19901128 (EN)

Application
EP 88909938 A 19881026

Priority
US 11356487 A 19871026

Abstract (en)
[origin: WO8904056A1] The present invention comprises a metal-oxide-semiconductor field-effect transistor (MOSFET) formed in silicon carbide (12). The doped source (10) and doped drain (11) are formed by high temperature ion implantation of dopant ions into the silicon carbide (12).

IPC 1-7
H01L 21/265; **H01L 29/78**; **H01L 29/167**

IPC 8 full level
H01L 29/78 (2006.01); **H01L 29/24** (2006.01)

CPC (source: EP KR)
H01L 29/1608 (2013.01 - EP); **H01L 29/772** (2013.01 - KR)

Citation (search report)

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- See references of WO 8904056A1

Designated contracting state (EPC)
DE FR GB IT NL SE

DOCDB simple family (publication)
WO 8904056 A1 19890505; CA 1313571 C 19930209; EP 0386085 A1 19900912; EP 0386085 A4 19901128; JP 2644028 B2 19970825; JP H03501670 A 19910411; KR 0137966 B1 19980601; KR 890702245 A 19891223

DOCDB simple family (application)
US 8803793 W 19881026; CA 581146 A 19881025; EP 88909938 A 19881026; JP 50917288 A 19881026; KR 890701157 A 19890626